Preliminary

TOSHIBA Multi Chip Discrete Device

HN7G01FU

Power Management Switch Application

Driver Circuit Application

Interface Circuit Application

Q1 (transistor): 2SA1955 equivalent
Q2 (MOS-FET): 2SK1830 equivalent

Q1 (transistor) Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-15	N/
Collector-emitter voltage	V _{CEO}	-12	(V)
Emitter-base voltage	V _{EBO}	-5	$(\checkmark\cancel{v})$
Collector current	IC	-400	mA
Base current	ΙΒ	-50	mA

Q2 (MOS-FET) Absolute Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V _{DS}	20	/ (v
Gate-source voltage	V _{GS} S	10	X
Drain current	<u>-</u> D(50	mA

Q1, Q2 Common Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power dissipation	P _C (Note 1)	200	mW
Junction temperature	Tį	125	ů
Storage temperature range	T _{stg}	-55~150	°C
		/ /	

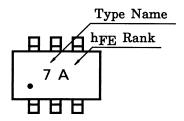
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions")"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

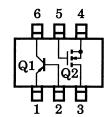
Note 1: Total rating

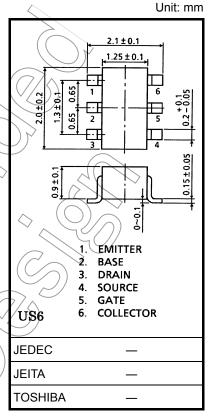
Marking

Note:



Pin Assignment (top view)





Weight: 6.8 mg (typ.)

Q1 (transistor) Electrical Characteristics (Ta = 25°C)

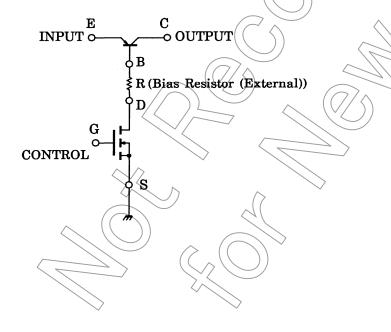
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -15 \text{ V}, I_E = 0$	_	_	-0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V, } I_C = 0$	_	_	-0.1	mA
DC current gain	h _{FE} (Note 2)	$V_{CE} = -2 \text{ V, I}_{C} = -10 \text{ mA}$	300	_	1000	
Collector-emitter saturation voltage	V _{CE} (sat) (1)	$I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$	(F) / 15	-30	mV
Collector-entitler Saturation voltage	V _{CE} (sat) (2)	$I_C = -200 \text{ mA}, I_B = -10 \text{ mA}$	>> <u></u>	-110	-250	1117
Base-emitter saturation voltage	V _{BE (sat)}	$I_C = -200 \text{ mA}, I_B = -10 \text{ mA}$	()	-0.87	-1.2	V

Note 2: hFE classification A: 300~600, B: 500~1000

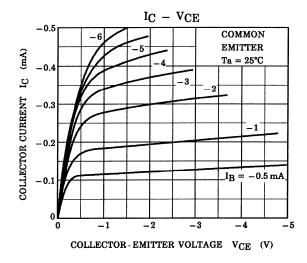
Q2 (MOS-FET) Electrical Characteristics (Ta = 25°C)

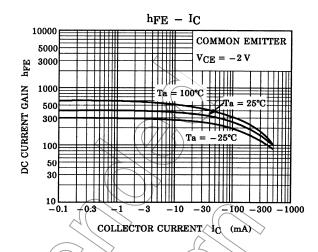
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Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = 10 \text{ V}, V_{DS} = 0$	\(14n) 1	μΑ
Drain-source breakdown voltage	V (BR) DSS	$I_D = 100 \mu A, V_{GS} = 0$	20		_	V
Drain current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	1	μΑ
Gate threshold voltage	V_{th}	V _{DS} = 3 V, I _D = 0.1 mA	0.5		1.5	٧
Forward transfer admittance	Yfs	V _{DS} = 3 V, I _D = 10 mA	20	_		mS
Drain-source ON resistance	R _{DS} (ON)	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	/ _	20	40	Ω

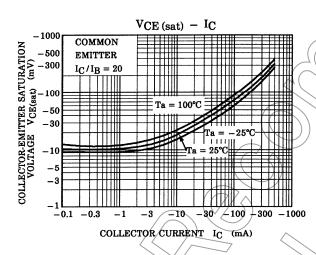
Application Example (power management switch)

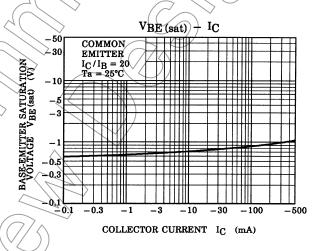


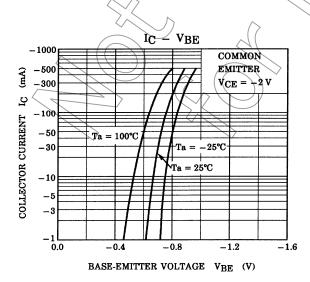
Transistor







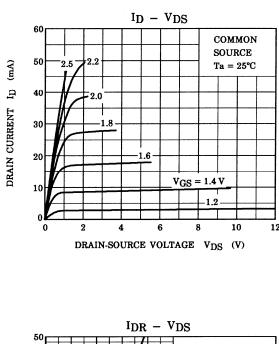


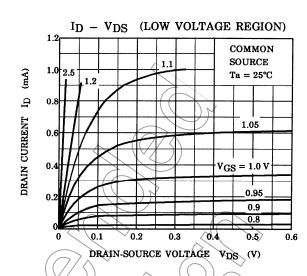


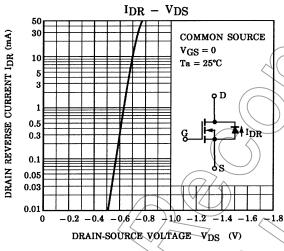
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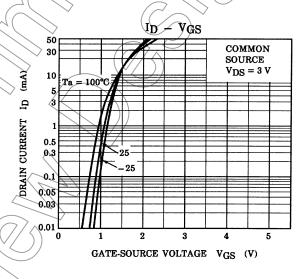
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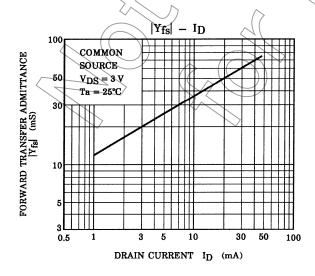
MOS-FET

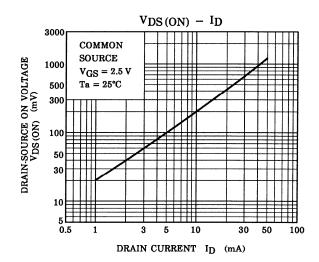












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